

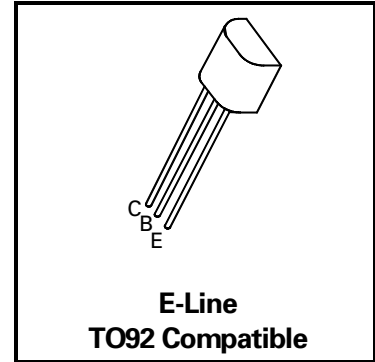
NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTORS

BCX38A/B/C

ISSUE 1 – MARCH 94

FEATURES

- * 60 Volt V_{CEO}
- * Gain of 10K at $I_C=0.5$ Amp
- * $P_{tot}=1$ Watt



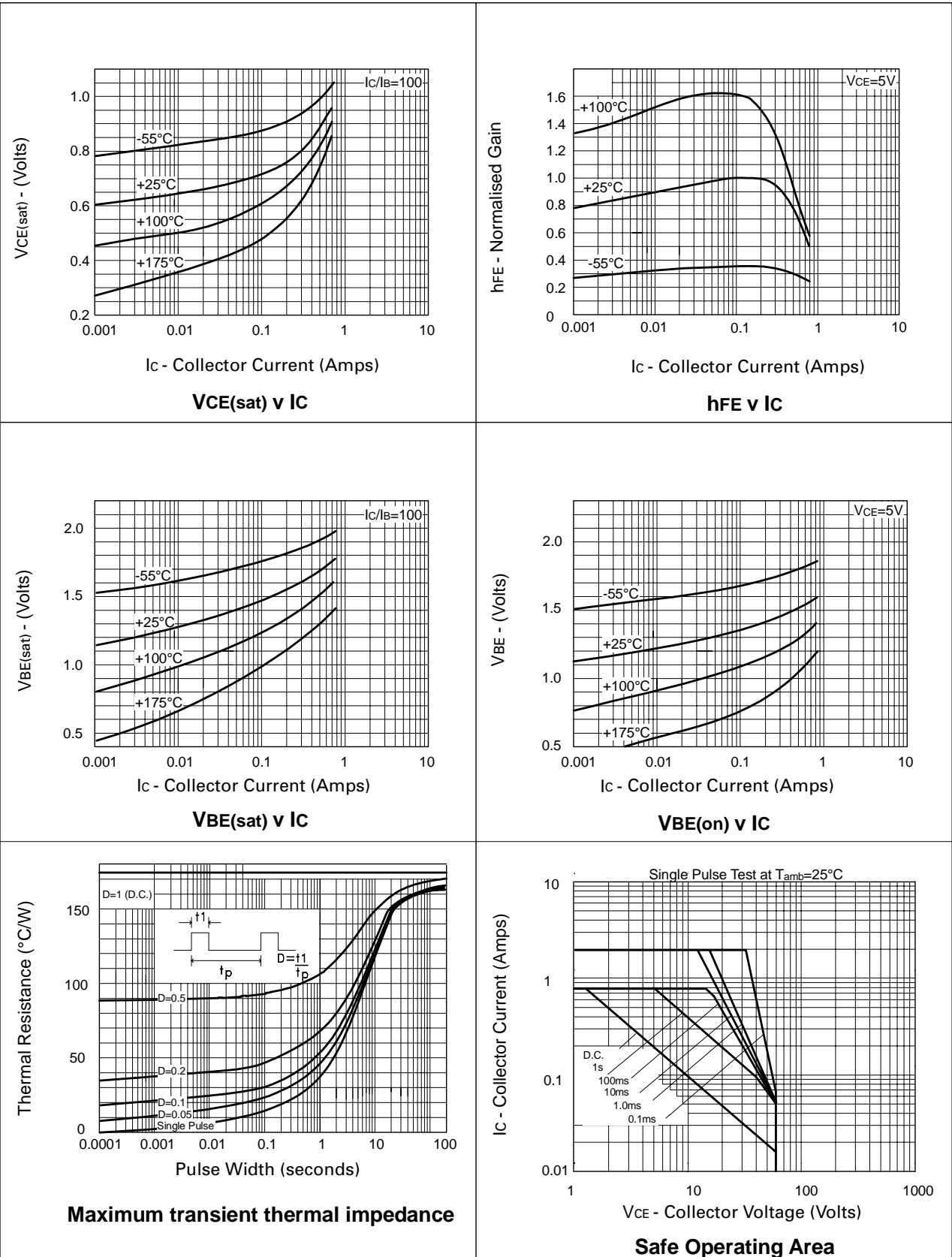
ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +200	$^{\circ}C$

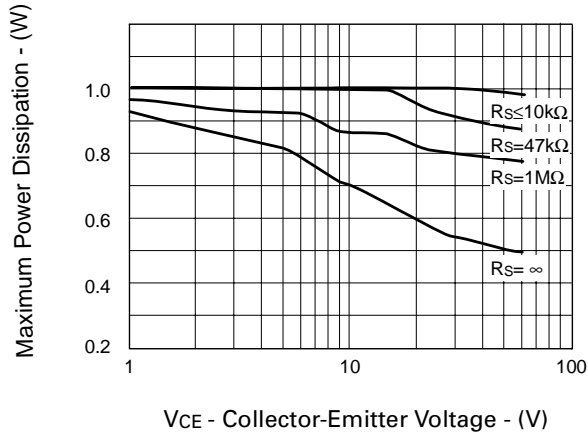
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80			V	$I_C=10\mu A, I_E=0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	60			V	$I_C=10mA, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=10\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=60V, I_E=0$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=8V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1.25	V	$I_C=800mA, I_B=8mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			1.8	V	$I_C=800mA, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	BCX38A	h_{FE}	500 1000			$I_C=100mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$
	BCX38B		2000 4000			$I_C=100mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$
	BCX38C		5000 10000			$I_C=100mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$

TYPICAL CHARACTERISTICS



BCX38A/B/C



The maximum permissible operational temperature can be obtained using the equation:

$$T_{amb(max)} = \frac{Power(max) - Power(actual)}{0.0057} + 25^{\circ}C$$

$T_{amb(max)}$ = Maximum operating ambient temperature

Power (max) = Maximum power dissipation figure, for a given V_{CE} and source resistance (R_S)

Power (actual) = Actual power dissipation in users circuit